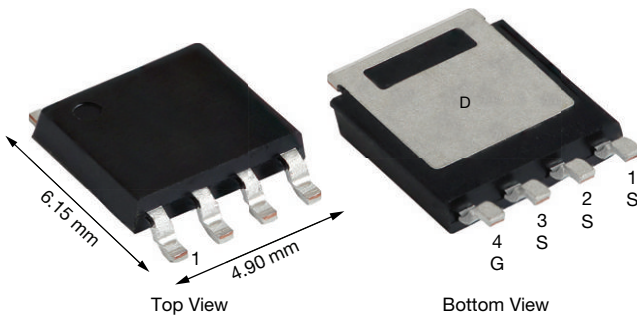
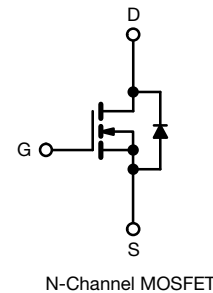


Automotive N-Channel 30 V (D-S) 175 °C MOSFET

PowerPAK® SO-8L

FEATURES

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Q_{gd}/Q_{gs} ratio < 1 optimizes switching characteristics
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

 AUTOMOTIVE
GRADE

RoHS
COMPLIANT
HALOGEN
FREE


N-Channel MOSFET

PRODUCT SUMMARY	
V _{DS} (V)	30
R _{DS(on)} (Ω) at V _{GS} = 10 V	0.00174
R _{DS(on)} (Ω) at V _{GS} = 4.5 V	0.00256
I _D (A) ^e	206
Configuration	Single

ORDERING INFORMATION	
Package	PowerPAK® SO-8L
Lead (Pb)-free and halogen-free	SQJ120ELP (for detailed order number please see www.vishay.com/doc?79776)

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-source voltage	V _{DS}	30	V		
Gate-source voltage	V _{GS}	± 20			
Continuous drain current ^e	I _D	T _C = 25 °C	206	A	
		T _C = 125 °C	119		
Continuous source current (diode conduction) ^e	I _S	118	A		
Pulsed drain current ^e	I _{DM}	700			
Single pulse avalanche current	I _{AS}	L = 0.1 mH	37		mJ
Single pulse avalanche energy			E _{AS}	68	
Maximum power dissipation ^{b, e}	P _D	T _C = 25 °C	130	W	
		T _C = 125 °C	43		
Operating junction and storage temperature range	T _J , T _{stg}	-55 to +175	°C		
Soldering recommendations (peak temperature) ^c		260			

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction-to-ambient	R _{thJA}	42	°C/W	
Junction-to-case (drain) ^d	R _{thJC}	1.15		

Notes

- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)
- See solder profile (www.vishay.com/doc?73257). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- As per JESD51-14
- Values based on R_{thJC} and T_C of 25 °C. Actual values achievable will be dependent on the thermal characteristics of the complete system



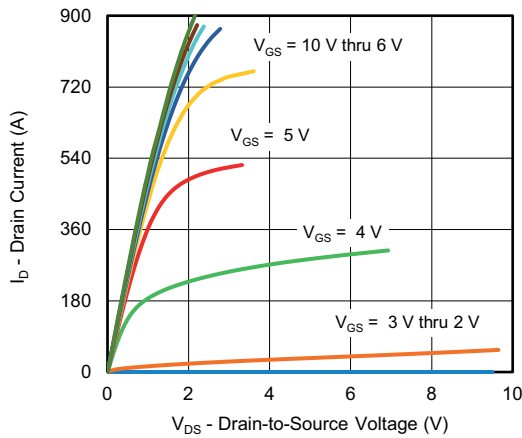
SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		30	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		1.5	2.0	2.5	
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 30 V	-	-	1	μA
		V _{GS} = 0 V	V _{DS} = 30 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 30 V, T _J = 175 °C	-	-	250	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	30	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 15 A	-	0.00145	0.00174	Ω
		V _{GS} = 10 V	I _D = 15 A, T _J = 125 °C	-	-	0.00265	
		V _{GS} = 10 V	I _D = 15 A, T _J = 175 °C	-	-	0.0031	
		V _{GS} = 4.5 V	I _D = 15 A	-	0.00205	0.00256	
Forward transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 40 A		-	180	-	S
Dynamic^b							
Input capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	4797	6716	pF
Output capacitance	C _{oss}			-	1708	2392	
Reverse transfer capacitance	C _{rss}			-	197	276	
Total gate charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 15 V, I _D = 15 A	-	74	111	nC
Gate-source charge ^c	Q _{gs}			-	13	-	
Gate-drain charge ^c	Q _{gd}			-	14	-	
Gate resistance	R _g	f = 1 MHz		0.8	2	3.2	Ω
Turn-on delay time ^c	t _{d(on)}	V _{DD} = 15 V, R _L = 1 Ω I _D ≅ 15 A, V _{GEN} = 10 V, R _g = 1 Ω		-	13	20	ns
Rise time ^c	t _r			-	6	9	
Turn-off delay time ^c	t _{d(off)}			-	42	63	
Fall time ^c	t _f			-	13	20	
Source-Drain Diode Ratings and Characteristics^b							
Pulsed current ^a	I _{SM}			-	-	472	A
Forward voltage	V _{SD}	I _F = 15 A, V _{GS} = 0 V		-	-	1.1	V
Body diode reverse recovery time	t _{rr}	I _F = 10 A, di/dt = 100 A/μs		-	44	88	ns
Body diode reverse recovery charge	Q _{rr}			-	38	76	nC
Reverse recovery fall time	t _a			-	22	-	ns
Reverse recovery rise time	t _b			-	23	-	
Body diode peak reverse recovery current	I _{RM(REC)}					-	-1.44

Notes

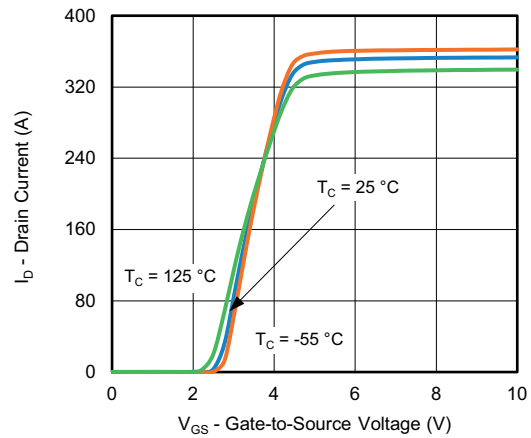
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

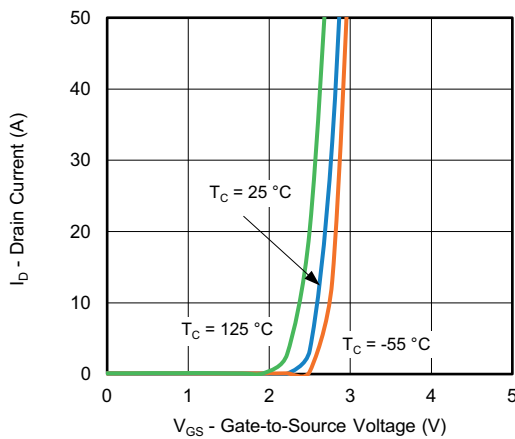
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



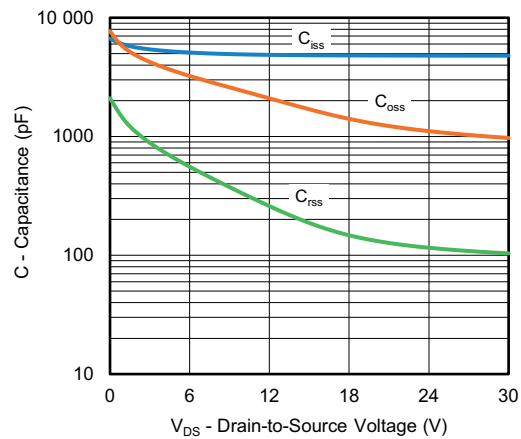
Output Characteristics



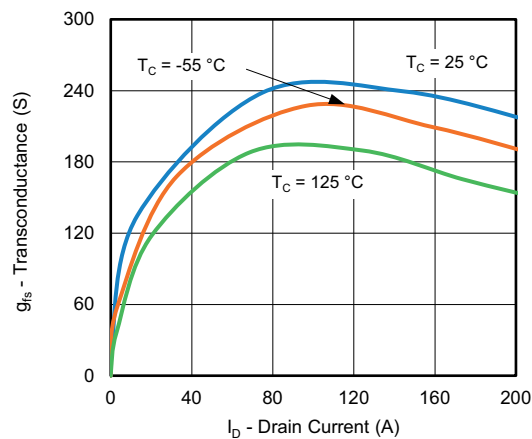
Transfer Characteristics



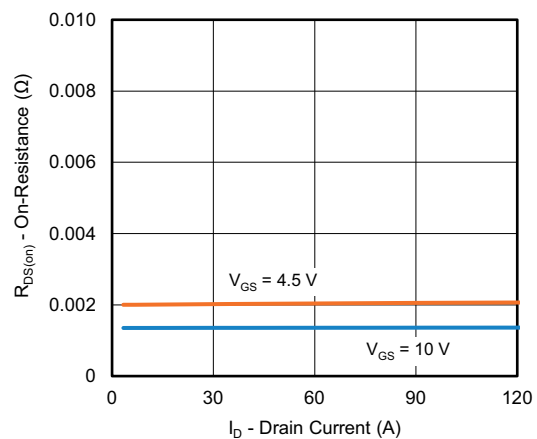
Transfer Characteristics



Capacitance



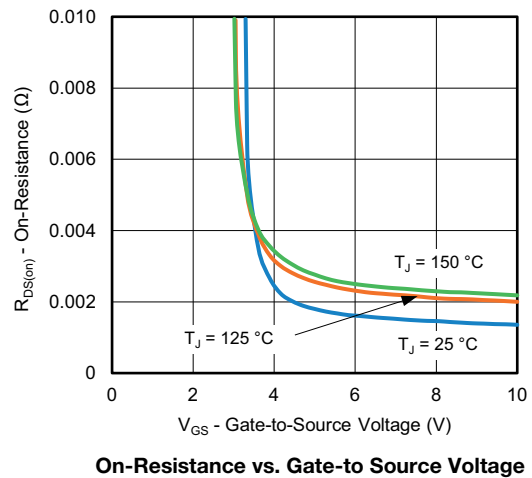
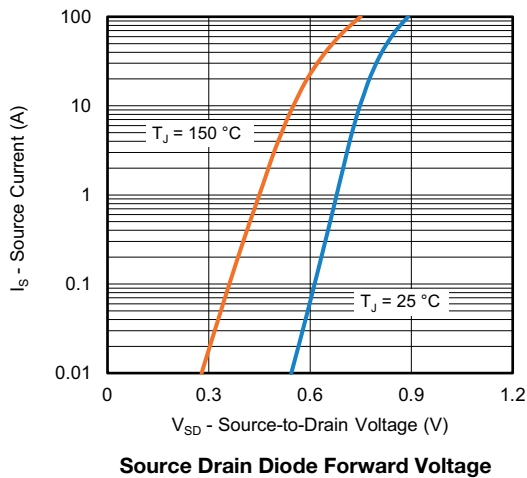
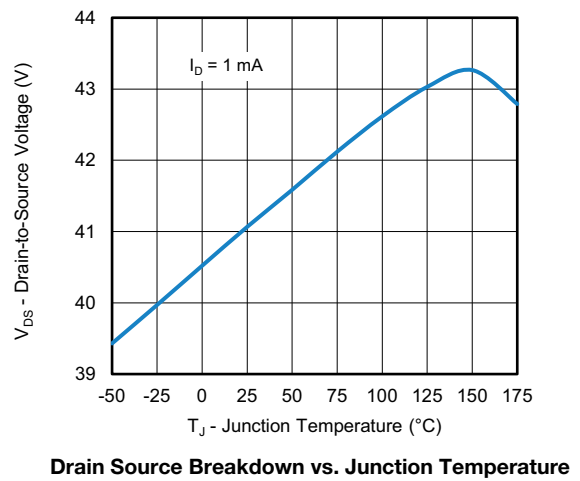
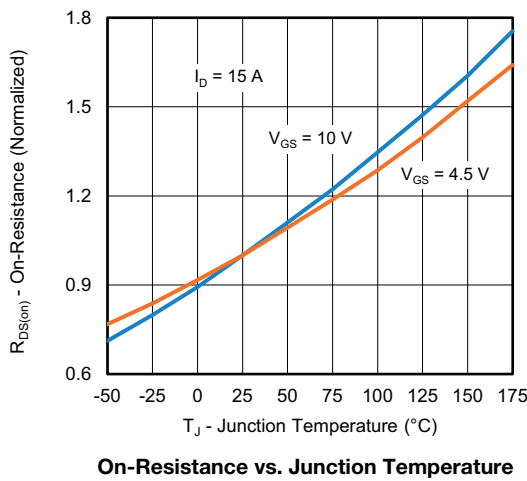
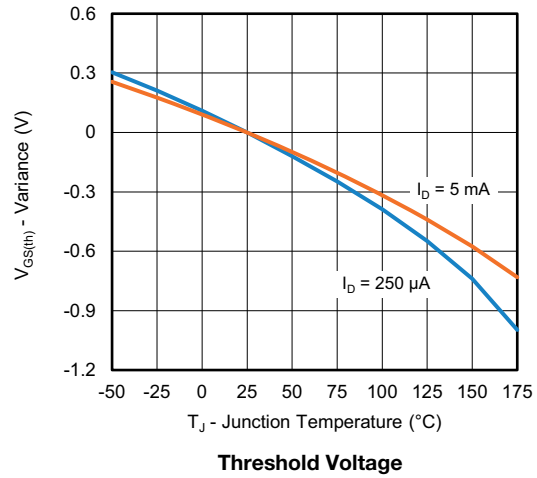
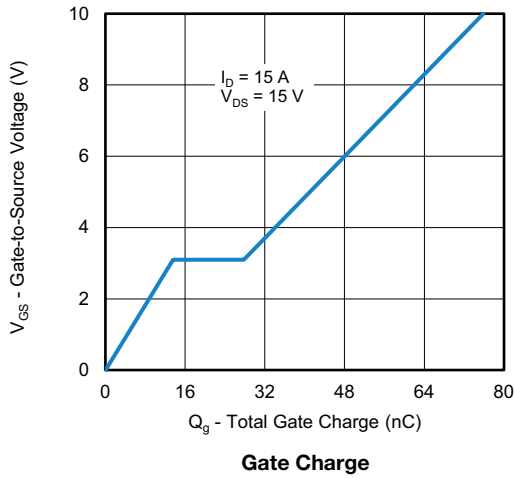
Transconductance

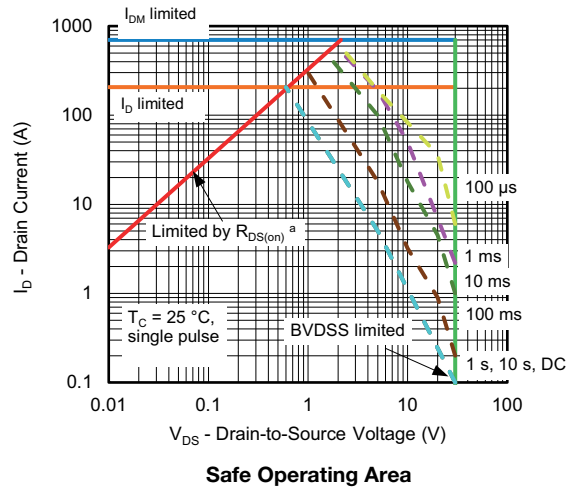


On-Resistance vs. Drain Current



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



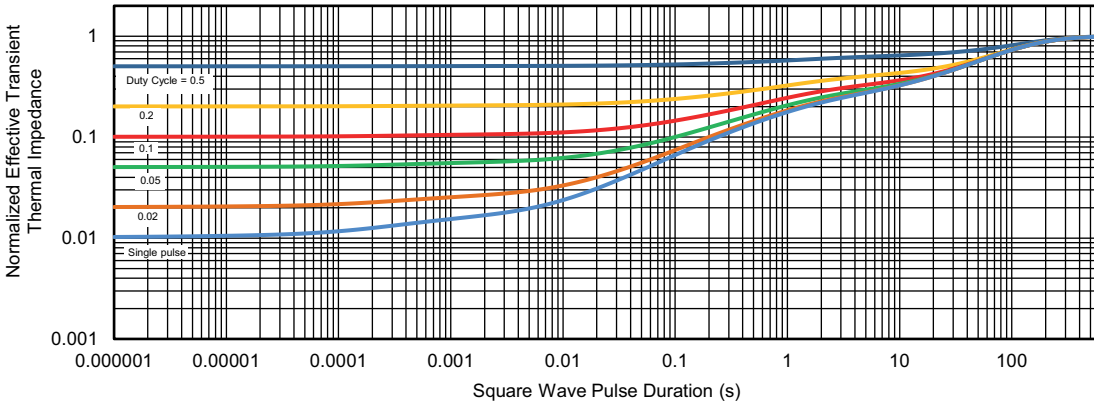


Note

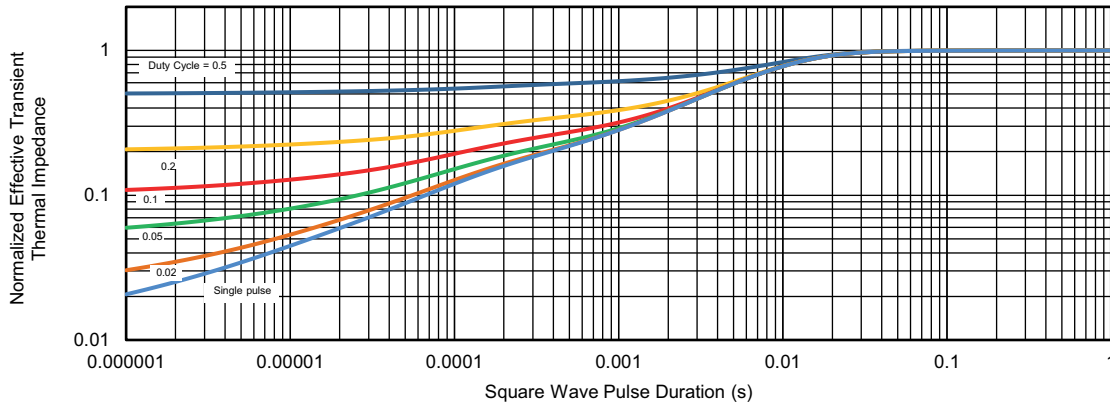
a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified



TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^\circ\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Case ($25\text{ }^\circ\text{C}$)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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